N-Ch MOSFET

General Description

The WSF60100 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF60100 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

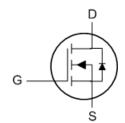
BVDSS	RDSON	ID
60V	6mΩ	98A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- LCD/LED back light

TO-252 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage 60		V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	100	Α	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	80	Α	
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	14	Α	
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	11	Α	
I _{DM}	Pulsed Drain Current ²	285	Α	
EAS	Single Pulse Avalanche Energy ³	182	mJ	
I _{AS}	Avalanche Current	60	Α	
P _D @T _C =25℃	Total Power Dissipation ⁴	150	W	
P _D @T _A =25℃	Total Power Dissipation ⁴	2.5	W	
T _{STG}	Storage Temperature Range -55 to 175		$^{\circ}$ C	
T_J	Operating Junction Temperature Range -55 to 175		°C	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-Ambient ¹		50	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		1	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0 V , I_D =250 u A	60			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25 $^{\circ}$ C , I _D =1mA		0.057		V/°C
D	Static Drain-Source On-Resistance ²	V_{GS} =10V , I_D =20A		6	7	0
$R_{DS(ON)}$		V _{GS} =10V , I _D =20A ,T _J =125 °C		8.4	10.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	\/ -\/ -250\	2	3	4	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-5.68		mV/℃
	Drain Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25°C			1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =55°C			5	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =20A		75		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		0.65	1.0	Ω
Q_g	Total Gate Charge (4.5V)			54	75	
Q_{gs}	Gate-Source Charge	V _{DS} =48V , V _{GS} =4.5V , I _D =15A		23	35	nC
Q_{gd}	Gate-Drain Charge			18	28	
T _{d(on)}	Turn-On Delay Time	V_{DD} =30V , V_{GS} =10V , R_{G} =3 Ω , RL=1.5 Ω .		19	24.4	
Tr	Rise Time			22	30	
T _{d(off)}	Turn-Off Delay Time			33	32	ns
T _f	Fall Time			6	10	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		4055		
C _{oss}	Output Capacitance			346		pF
C _{rss}	Reverse Transfer Capacitance			18		

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V , L=0.1mH , I _{AS} =60A	100			mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			46	Α
I _{SM}	Pulsed Source Current ^{2,6}				60	Α
V_{SD}	Diode Forward Voltage ²	V_{GS} =0V , I_{S} =1A , T_{J} =25 $^{\circ}$ C			1	V
t _{rr}	Reverse Recovery Time	IF=20A ,dI/dt=500A/μs,TJ=25℃		26		nS
Qrr	Reverse Recovery Charge			126		nC

Note:

- 1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V,L=0.1mH, I_{AS} =60A
- 4. The power dissipation is limited by 150 °C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

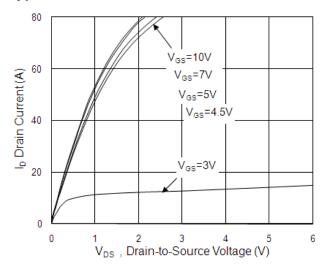


Fig.1 Typical Output Characteristics

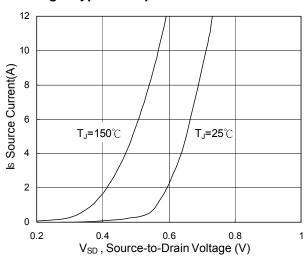


Fig.3 Forward Characteristics of Reverse

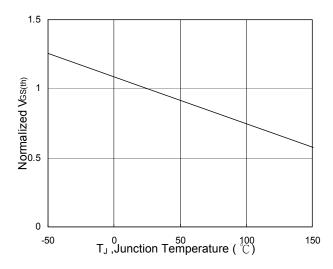


Fig.5 Normalized V_{GS(th)} v.s T_J

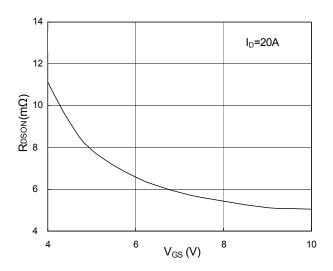


Fig.2 On-Resistance v.s Gate-Source

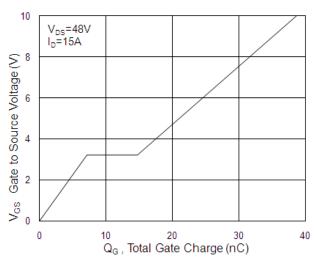


Fig.4 Gate-Charge Characteristics

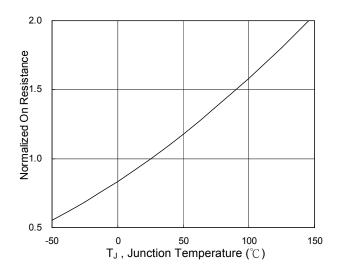
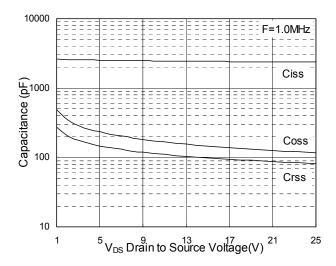


Fig.6 Normalized R_{DSON} v.s T_J







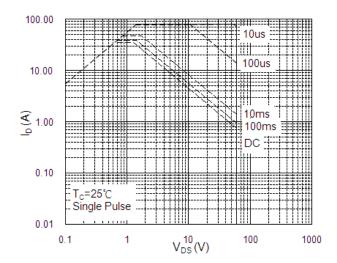


Fig.7 Capacitance

Fig.8 Safe Operating Area

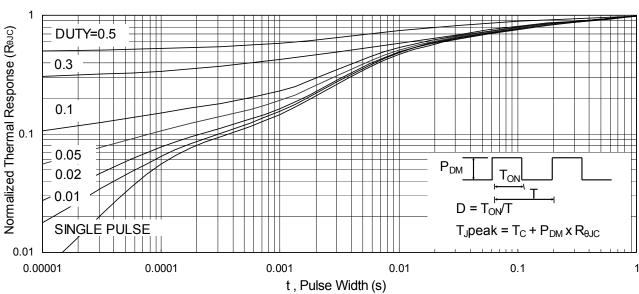


Fig.9 Normalized Maximum Transient Thermal Impedance

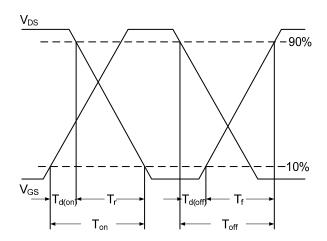


Fig.10 Switching Time Waveform

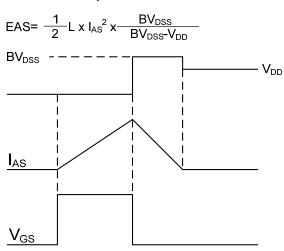


Fig.11 Unclamped Inductive Switching Waveform



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